

MJE13003L1 (3DD13003L1)

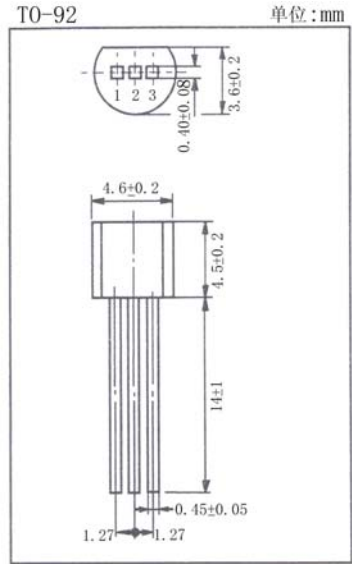
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO}	900	V
V _{CEO}	530	V
V _{EBO}	9.0	V
I _C	1.5	A
I _{CP}	3.0	A
P _C (Ta=25°C)	1.0	W
T _j	150	°C
T _{stg}	-55~150	°C



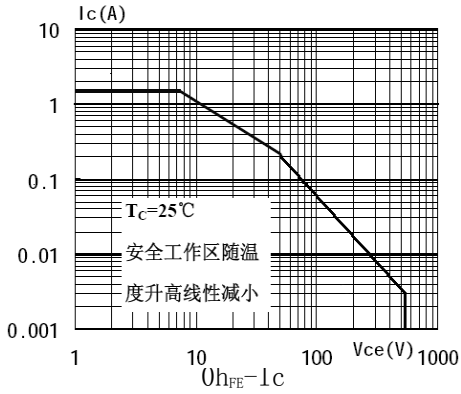
引脚：1. E 2. C 3. B

电性能参数/Electrical characteristics(Ta=25°C)

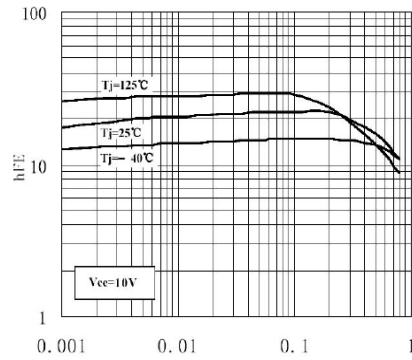
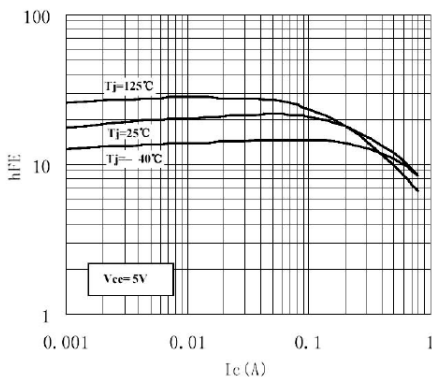
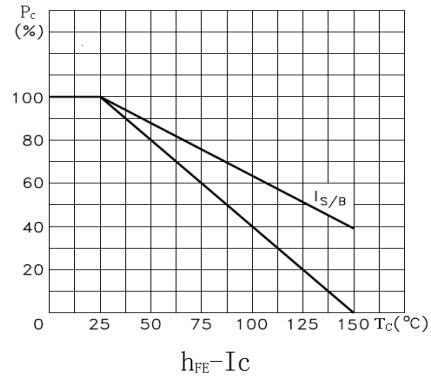
参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V _{CBO}	I _C =1mA	I _E =0	900			V
V _{CEO}	I _C =10mA	I _B =0	530			V
V _{EBO}	I _E =1mA	I _C =0	9			V
I _{CBO}	V _{CB} =900V	I _E =0			0.1	mA
I _{CEO}	V _{CE} =530V	I _B =0			0.1	mA
I _{EBO}	V _{EB} =9.0V	I _C =0			0.1	mA
h _{FE(1)}	V _{CE} =10V	I _C =400mA	10		40	
h _{FE(2)}	V _{CE} =10V	I _C =1.0mA	15			
h _{FE(3)}	V _{CE} =10V	I _C =1.0A	6		40	
V _{CE(sat) (1)}	I _C =0.5A	I _B =0.1A			0.8	V
V _{CE(sat) (2)}	I _C =1.5A	I _B =0.5A			2.5	V
V _{BE(sat)}	I _C =0.5A	I _B =0.1A			1.2	V
f _T	V _{CE} =10V	I _C =0.1A	f=1.0MHz	5.0		MHz
t _f	V _{CE} =5V	I _C =0.25A			1.2	μs
t _s	(UI9600)				5.0	μs

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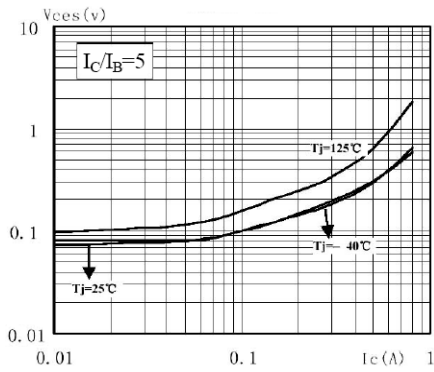
SOA (DC)



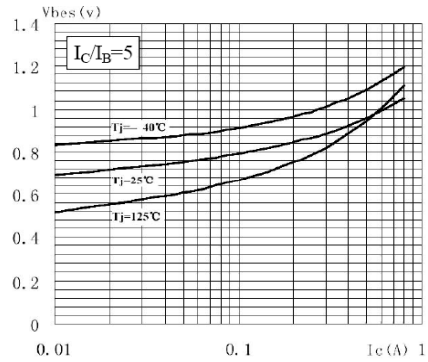
$P_c - T_c$



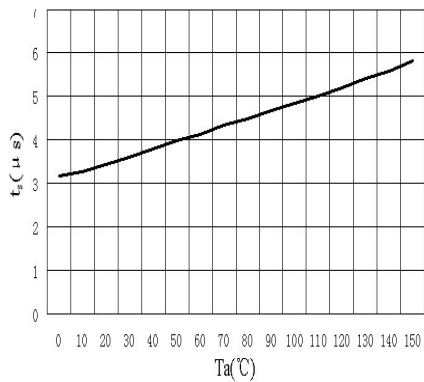
$V_{ces} - I_c$



$V_{bes} - I_c$



$t_s - T_a$



$h_{FE} - T_a$

